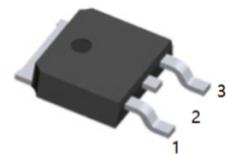


General Description

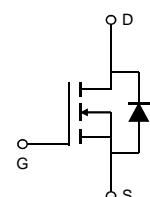
- Very Low $R_{DS(ON)}$
- Low Gate Charge
- Optimized for fast-switching applications



TO-252(DPAK) top view

Application

- Synchronous Rectification in DC/DC and AC/DC Converters
- Isolated DC/DC Converters in Telecom and Industrial
- $V_{DS(V)} = 100V$
- $I_D = 7A$ ($V_{GS} = 10V$)
- $R_{DS(ON)} < 140m\Omega$ ($V_{GS} = 10V$)
- $R_{DS(ON)} < 176m\Omega$ ($V_{GS} = 4.5V$)



Absolute Maximum Ratings $T_A=25^\circ C$ unless otherwise noted

Parameter	Symbol	Maximum	Units	
Drain-Source Voltage	V_{DS}	100	V	
Gate-Source Voltage	V_{GS}	± 20	V	
Continuous Drain Current	I_D	7	A	
$T_C=25^\circ C$		5		
Pulsed Drain Current ^C	I_{DM}	10		
Continuous Drain Current	I_{DSM}	3.5	A	
$T_A=70^\circ C$		3		
Avalanche Current ^C	I_{AS}	3	A	
Avalanche energy $L=0.1mH$ ^C	E_{AS}	0.5	mJ	
V_{DS} Spike	10us	V_{SPIKE}	120	V
Power Dissipation ^B	P_D	17	W	
$T_C=100^\circ C$		8.5		
Power Dissipation ^A	P_{DSM}	5.0	W	
$T_A=70^\circ C$		3.2		
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 175	°C	

Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	20	25	°C/W
Maximum Junction-to-Ambient ^{AD}		40	50	°C/W
Maximum Junction-to-Case	Steady-State	$R_{\theta JC}$	7.3	°C/W

Electrical Characteristics ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
BV_{DSS}	Drain-Source Breakdown Voltage	$I_D=250\mu\text{A}, V_{GS}=0\text{V}$	100			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=100\text{V}, V_{GS}=0\text{V}$ $T_J=55^\circ\text{C}$		1	5	μA
I_{GSS}	Gate-Body leakage current	$V_{DS}=0\text{V}, V_{GS}=\pm 20\text{V}$			± 100	nA
$V_{\text{GS(th)}}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu\text{A}$	1.7	2.2	2.7	V
$R_{\text{DS(ON)}}$	Static Drain-Source On-Resistance	$V_{GS}=10\text{V}, I_D=5\text{A}$		117	140	$\text{m}\Omega$
		$V_{GS}=4.5\text{V}, I_D=3\text{A}$		140	176	$\text{m}\Omega$
g_{FS}	Forward Transconductance	$V_{DS}=5\text{V}, I_D=5\text{A}$		8.5		S
V_{SD}	Diode Forward Voltage	$I_S=1\text{A}, V_{GS}=0\text{V}$		0.8	1.1	V
I_S	Maximum Body-Diode Continuous Current				7	A
C_{iss}	Input Capacitance	$V_{GS}=0\text{V}, V_{DS}=50\text{V}, f=1\text{MHz}$		250	310	pF
C_{oss}	Output Capacitance			19	30	pF
C_{rss}	Reverse Transfer Capacitance			2.5	8	pF
R_g	Gate resistance	$f=1\text{MHz}$	5	10.5	16	Ω
$Q_g(10\text{V})$	Total Gate Charge	$V_{GS}=10\text{V}, V_{DS}=50\text{V}, I_D=5\text{A}$		3.8	10	nC
$Q_g(4.5\text{V})$	Total Gate Charge			1.8	6	nC
Q_{gs}	Gate Source Charge			0.8		nC
Q_{gd}	Gate Drain Charge			0.8		nC
$t_{D(\text{on})}$	Turn-On Delay Time	$V_{GS}=10\text{V}, V_{DS}=50\text{V}, R_L=10\Omega, R_{\text{GEN}}=3\Omega$		5		ns
t_r	Turn-On Rise Time			3		ns
$t_{D(\text{off})}$	Turn-Off Delay Time			19		ns
t_f	Turn-Off Fall Time			5		ns
t_{rr}	Body Diode Reverse Recovery Time	$I_F=5\text{A}, dI/dt=500\text{A}/\mu\text{s}$		16		ns
Q_{rr}	Body Diode Reverse Recovery Charge	$I_F=5\text{A}, dI/dt=500\text{A}/\mu\text{s}$		52		nC

A. The value of R_{JJA} is measured with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25^\circ\text{C}$. The Power dissipation P_{DSM} is based on $R_{\text{JJA}} \leq 10\text{s}$ and the maximum allowed junction temperature of 150°C . The value in any given application depends on the user's specific board design, and the maximum temperature of 175°C may be used if the PCB allows it.

B. The power dissipation P_D is based on $T_{J(\text{MAX})}=175^\circ\text{C}$, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

C. Single pulse width limited by junction temperature $T_{J(\text{MAX})}=175^\circ\text{C}$.

D. The R_{JJA} is the sum of the thermal impedance from junction to case R_{JJC} and case to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using <300μs pulses, duty cycle 0.5% max.

F. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of $T_{J(\text{MAX})}=175^\circ\text{C}$. The SOA curve provides a single pulse rating.

G. The maximum current rating is package limited.

H. These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

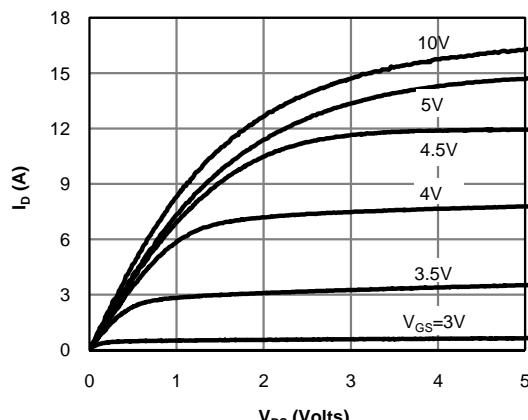


Figure 1: On-Region Characteristics (Note E)

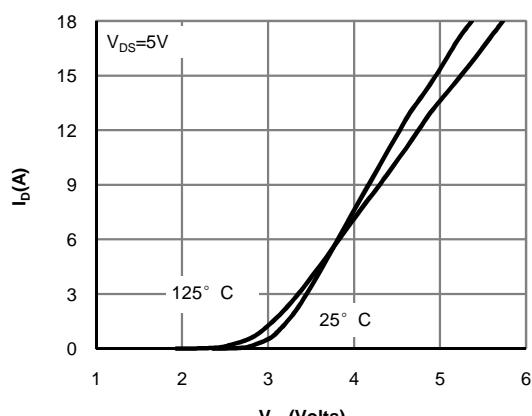


Figure 2: Transfer Characteristics (Note E)

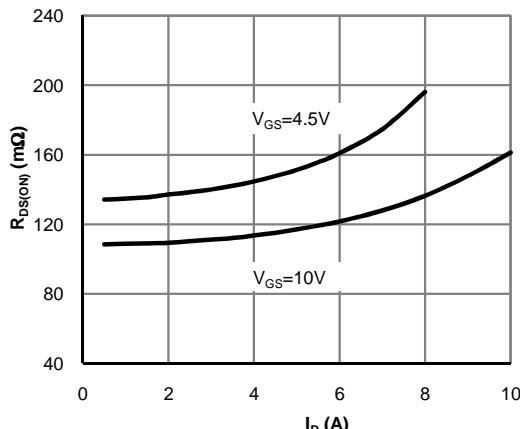
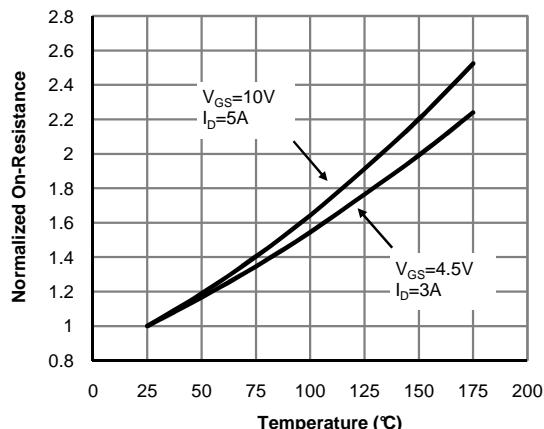
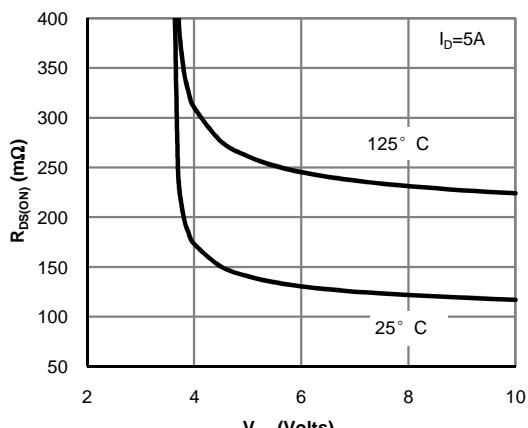


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)



**Figure 4: On-Resistance vs. Junction Temperature
(Note E)**



**Figure 5: On-Resistance vs. Gate-Source Voltage
(Note E)**

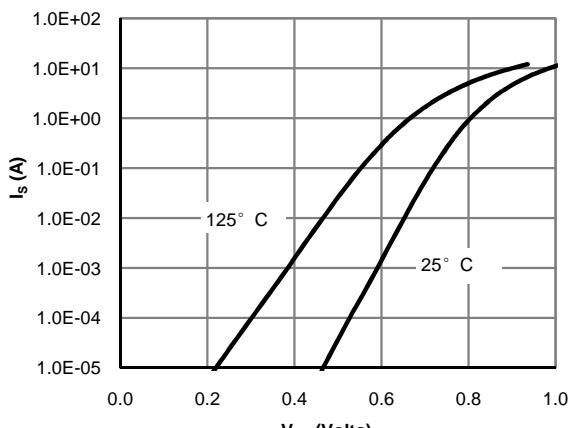
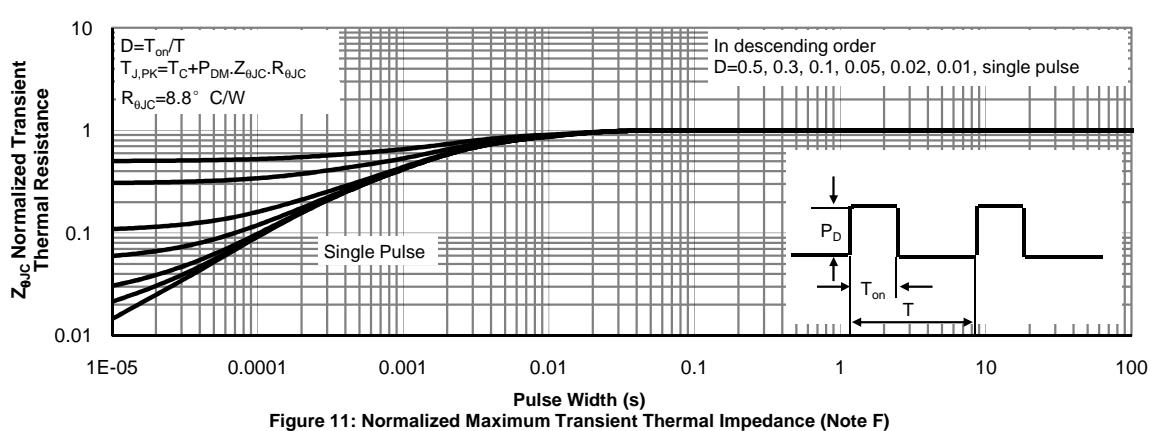
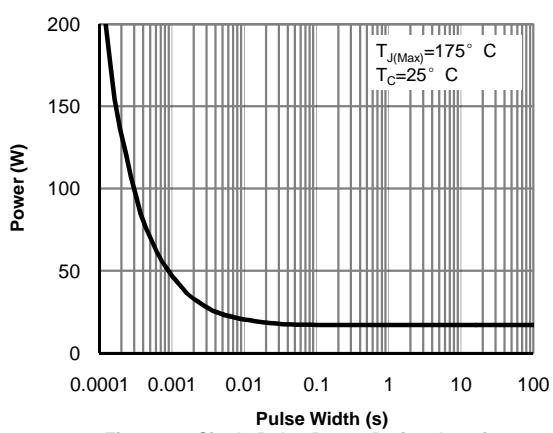
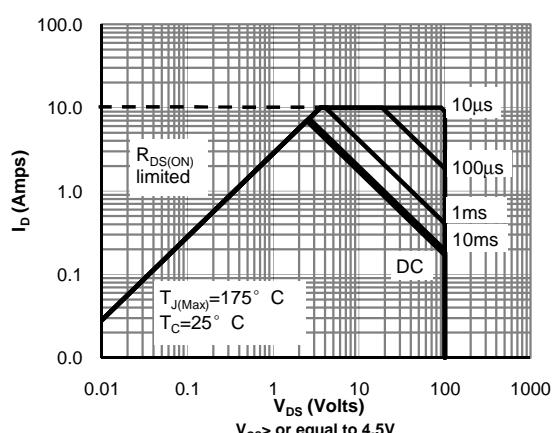
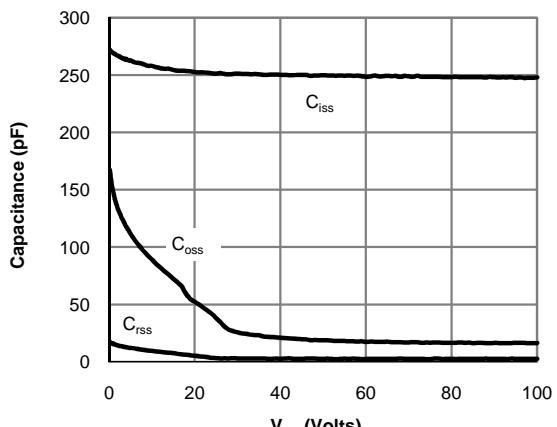
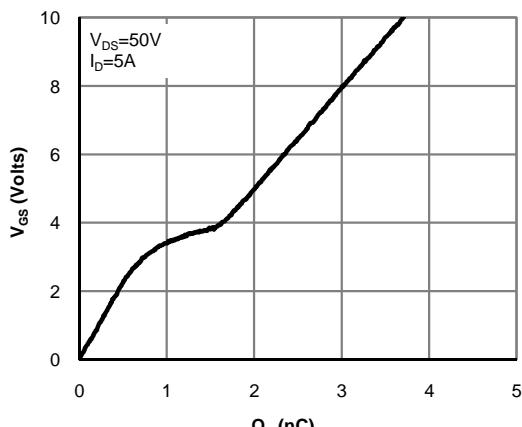


Figure 6: Body-Diode Characteristics (Note E)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS



TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

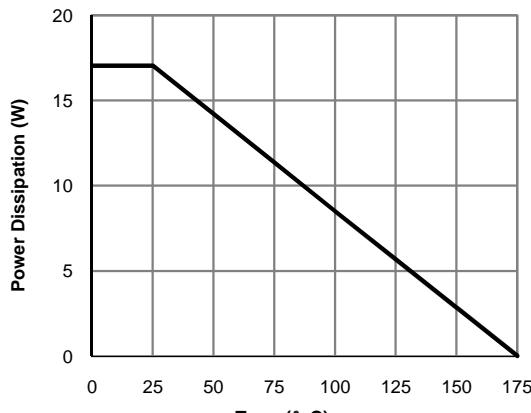


Figure 12: Power De-rating (Note F)

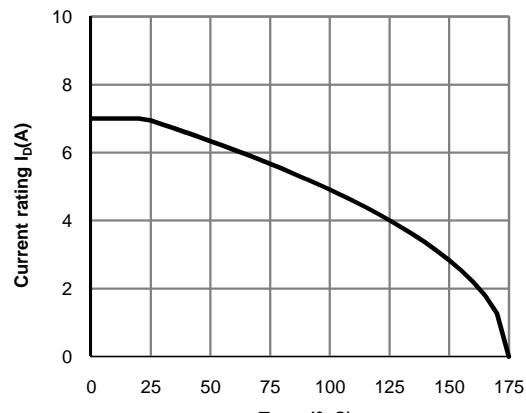


Figure 13: Current De-rating (Note F)

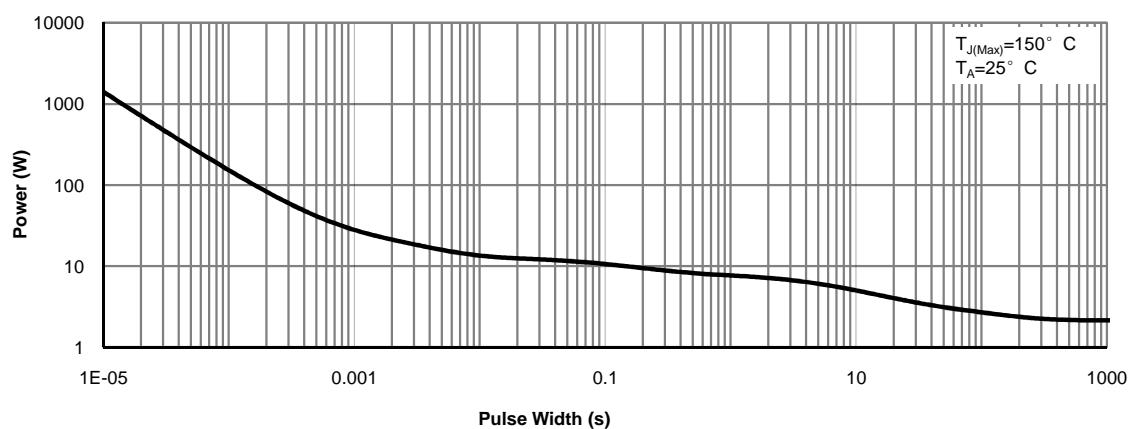


Figure 14: Single Pulse Power Rating Junction-to-Ambient (Note H)

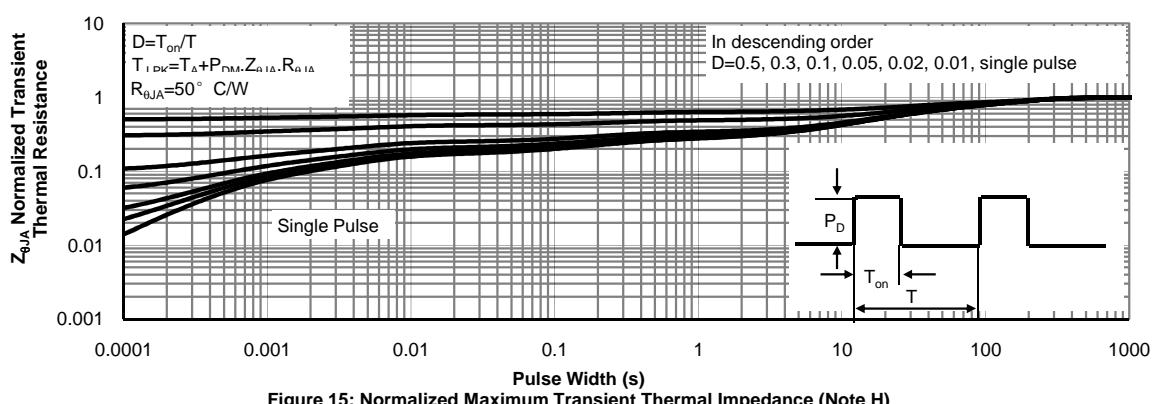
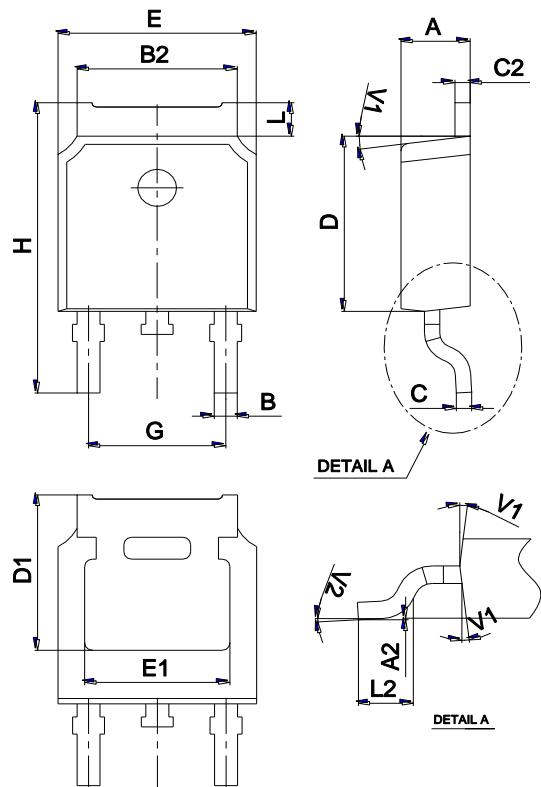
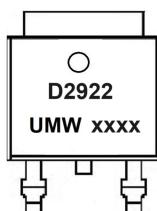


Figure 15: Normalized Maximum Transient Thermal Impedance (Note H)

Package Mechanical Data TO-252

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°

Marking**Ordering information**

Order code	Package	Baseqty	Deliverymode
UMW AOD2922	TO-252	2500	Tape and reel